

Standard Rectifier

$$V_{RRM} = 1600\text{ V}$$

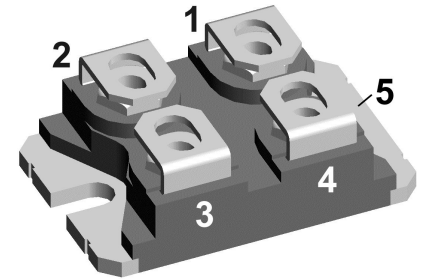
$$I_{FAV} = 2 \times 50\text{ A}$$

$$V_F = 1.13\text{ V}$$

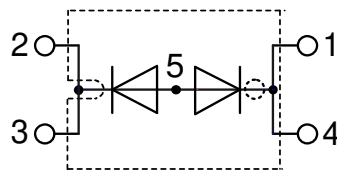
Common Anode

Part number

DMA100A1600NB



Backside: anode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification

Package: SOT-227UI (minibloc)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

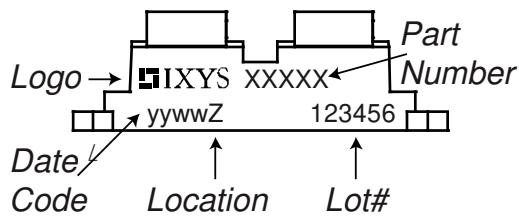
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					1700	V
V_{RRM}	max. repetitive reverse blocking voltage					1600	V
I_R	reverse current	$V_R = 1600$ V		$T_{VJ} = 25^\circ\text{C}$		100	μA
		$V_R = 1600$ V		$T_{VJ} = 150^\circ\text{C}$		1.5	mA
V_F	forward voltage drop	$I_F = 50$ A		$T_{VJ} = 25^\circ\text{C}$		1.19	V
		$I_F = 100$ A				1.39	V
		$I_F = 50$ A		$T_{VJ} = 125^\circ\text{C}$		1.13	V
		$I_F = 100$ A				1.39	V
I_{FAV}	average forward current	$T_C = 95^\circ\text{C}$		$T_{VJ} = 150^\circ\text{C}$		50	A
		rectangular	d = 0.5				
V_{FO}	threshold voltage			$T_{VJ} = 150^\circ\text{C}$		0.86	V
r_F	slope resistance					5.3	m Ω
		} for power loss calculation only					
R_{thJC}	thermal resistance junction to case					0.6	K/W
R_{thCH}	thermal resistance case to heatsink				0.1		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		210	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		850	A
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		920	A
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		725	A
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		780	A
I^2t	value for fusing	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		3.62	kA ² s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		3.52	kA ² s
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		2.63	kA ² s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		2.53	kA ² s
C_J	junction capacitance	$V_R = 400$ V; f = 1 MHz		$T_{VJ} = 25^\circ\text{C}$		28	pF



Package SOT-227UI (minibloc)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			200	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				30		g
M_D	mounting torque		1.1		1.5	Nm
M_T	terminal torque		1.1		1.5	Nm

Product Marking



Part description

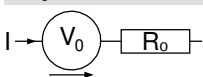
- D = Diode
- M = Standard Rectifier
- A = (up to 1800V)
- 100 = Current Rating [A]
- A = Common Anode
- 1600 = Reverse Voltage [V]
- NB = SOT-227UI (minibloc)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DMA100A1600NB	DMA100A1600NB	Tube	10	526693

Equivalent Circuits for Simulation

** on die level*

$T_{VJ} = 150^{\circ}C$

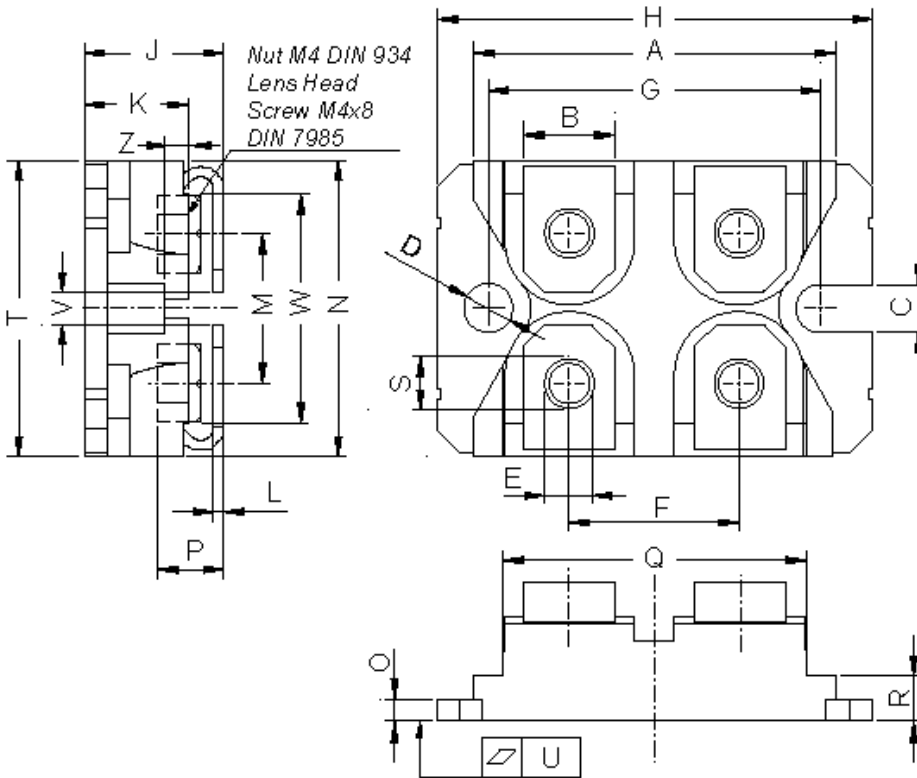


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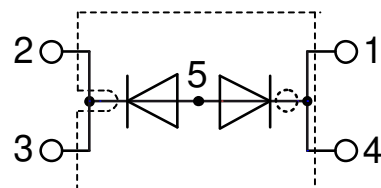
$V_{0\ max}$	threshold voltage	0.86	V
$R_{0\ max}$	slope resistance *	3.4	mΩ



Outlines SOT-227UI (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



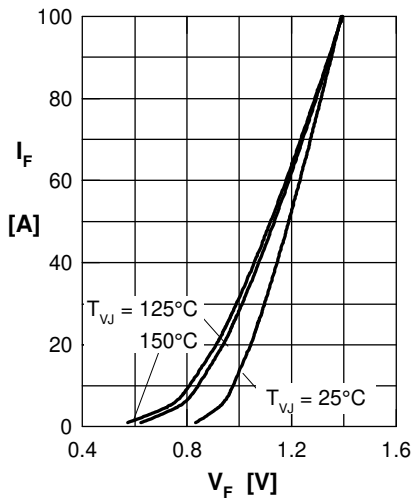
Rectifier


Fig. 1 Forward current versus voltage drop per diode

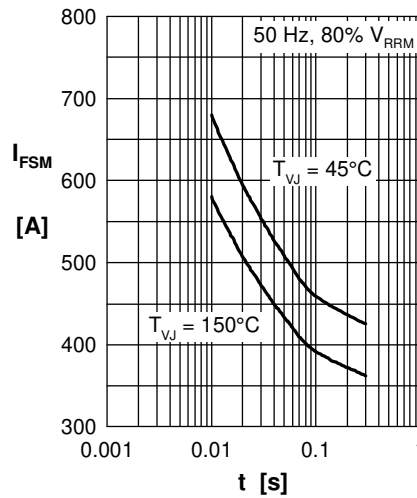


Fig. 2 Surge overload current

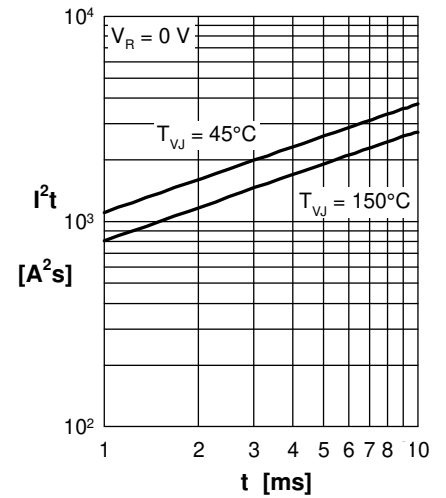
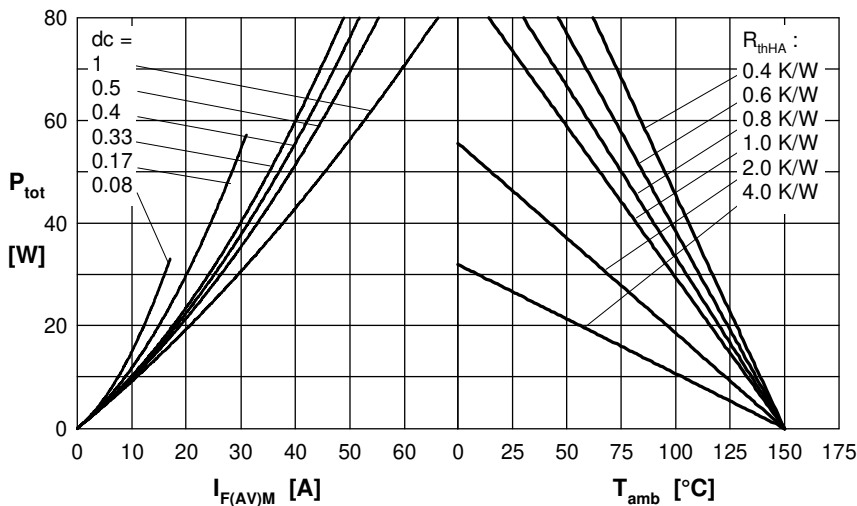

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. direct output current & ambient temperature

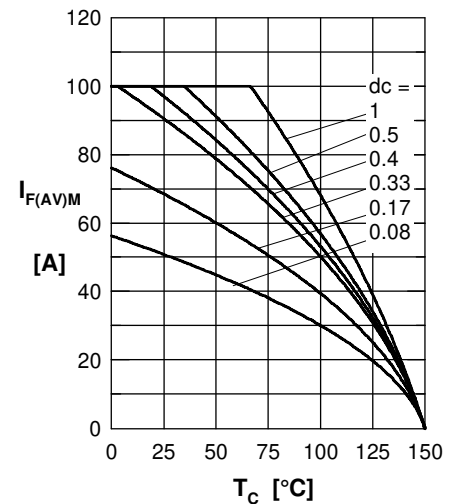


Fig. 5 Max. forward current versus case temperature

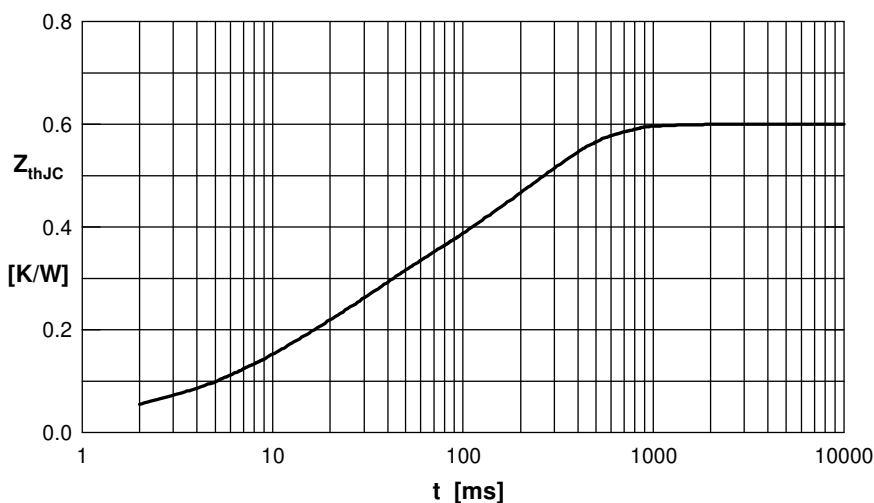


Fig. 6 Transient thermal impedance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0240	0.01000
2	0.0160	0.00001
3	0.0500	0.00500
4	0.1800	0.02300
5	0.3300	0.22000